

Part Number: L-93DP3BT

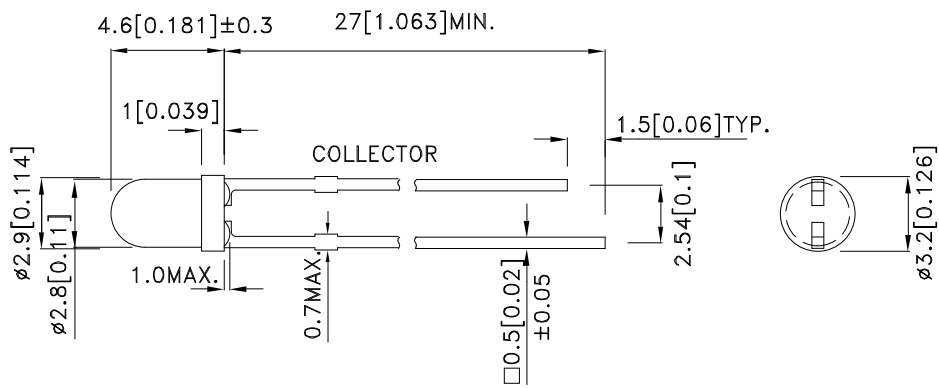
### Features

- MECHANICALLY AND SPECTRALLY MATCHED TO THE INFRARED EMITTING LED LAMP.
- BLUE TRANSPARENT LENS.
- RoHS COMPLIANT.

### Description

Made with NPN silicon phototransistor chips.

### Package Dimensions



#### Notes:

1. All dimensions are in millimeters (inches).
2. Tolerance is ±0.25(0.01") unless otherwise noted.
3. Lead spacing is measured where the leads emerge from the package.
4. Specifications are subject to change without notice.



## Electrical / Optical Characteristics at TA=25°C

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
V <sub>BR CEO</sub>	Collector-to-Emitter Breakdown Voltage	30			V	I <sub>C</sub> =100uA E <sub>e</sub> =0mW/c m <sup>2</sup>
V <sub>BR ECO</sub>	Emitter-to-Collector Breakdown Voltage	5			V	I <sub>E</sub> =100uA E <sub>e</sub> =0mW/c m <sup>2</sup>
V <sub>CE (SAT)</sub>	Collector-to-Emitter Saturation Voltage			0.8	V	I <sub>C</sub> =2mA E <sub>e</sub> =20mW/c m <sup>2</sup>
I <sub>CEO</sub>	Collector Dark Current			100	nA	V <sub>CE</sub> =10V E <sub>e</sub> =0mW/c m <sup>2</sup>
T <sub>R</sub>	Rise Time (10% to 90% )		15		us	V <sub>CE</sub> = 5V I <sub>C</sub> =1mA R <sub>L</sub> =1000Ω
T <sub>F</sub>	Fall Time (90% to 10% )		15		us	
I <sub>(ON)</sub>	On State Collector Current	0.07	0.35		mA	V <sub>CE</sub> = 5V E <sub>e</sub> =1mW/c m <sup>2</sup> λ=940nm

## Absolute Maximum Ratings at TA=25°C

Parameter	Max. Ratings
Collector-to-Emitter Voltage	30V
Emitter-to-Collector Voltage	5V
Power Dissipation at (or below) 25°C Free Air Temperature	100mW
Operating Temperature	-40°C To +85°C
Storage Temperature	-40°C To +85°C
Lead Soldering Temperature (>5mm for 5sec)	260°C